	Туре	L#	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	0	((light adj emitting adj diode) laser) and (second adj n adj type adj layer) and gaas and (sapphire adj substrate) and piezoelectric	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 13:48
2	BRS <sup>.</sup>	L2	2	((light adj emitting adj diode) laser) and (second adj n adj type adj layer) and gaas and (sapphire adj substrate)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 11:41
3	BRS	L3	38	((light adj emitting adj diode) laser) and gaas and (sapphire adj substrate) and piezoelectric	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 11:42
4	BRS <sub>.</sub>	L4	158	((light adj emitting adj	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:28
5	BRS	<b>L</b> 5	0	257/13/ccls. and piezoelectric	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:28
6	BRS	L6	0	257/13/ccls.	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:28

	Туре	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	<b>L</b> 7	340	257/13.ccls.	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:28
8	BRS	L8	0	7 and @ay,2000	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:29
9	BRS	L9	317	7 and @ay<2000	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:40
10	BRS	L10	5	9 and piezoelectric	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:29
11	BRS	L11	0	9 and (buried adj active adj layer)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:40
12	BRS	L12	0	9 and (offset adj active adj layer)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:48

	Туре	L#	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	18		USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:51
14	BRS	L14	212	372/45.ccls. and (first adj conductivity) and (second adj conductivity) and (quantum adj well)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 12:53
15	BRS	L15	206	14 and @ay<2000		2002/11/12 12:54
16	BRS	L16	1156	((light adj emitting adj diode) laser) and unipolar	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 13:49
17	BRS	L17	69	16 and (gaas gaalas algaas) and @ay<2000	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/11/12 13:50